

SPP6507

DESCRIPTION

The SPP6507 is the Dual P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

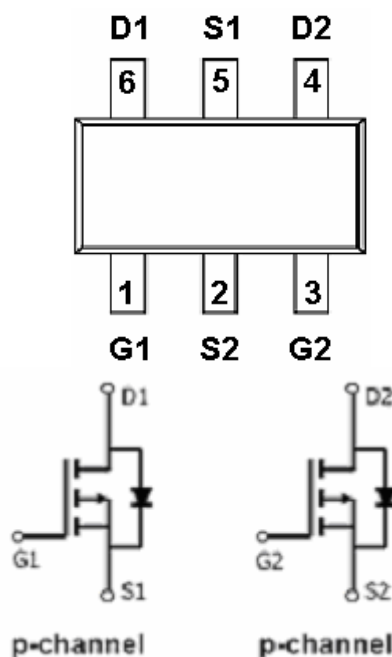
FEATURES

- ◆ P-Channel
 - 30V/-2.8A, $R_{DS(ON)}=105m\Omega@V_{GS}=-10V$
 - 30V/-2.5A, $R_{DS(ON)}=115m\Omega@V_{GS}=-4.5V$
 - 30V/-1.5A, $R_{DS(ON)}=150m\Omega@V_{GS}=-2.5V$
 - 30V/-1.0A, $R_{DS(ON)}=215m\Omega@V_{GS}=-1.8V$
- ◆ Super high density cell design for extremely low RDS (ON)
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23-6L package design

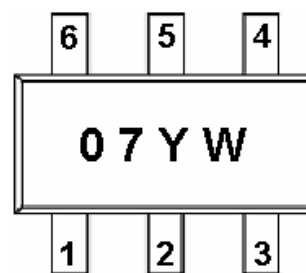
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-23-6L)



PART MARKING



Y : Year Code
W : Week Code

SPP6507

PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP6507S26RG	SOT-23- 6L	07YW

※ Week Code : A ~ Z (1 ~ 26) ; a ~ z (27 ~ 52)

※ SPP6507S26RG : Tape Reel ; Pb – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	-2.8
		TA=70°C	-2.1
Pulsed Drain Current	I _{DM}	-8	A
Continuous Source Current(Diode Conduction)	I _S	-1.4	A
Power Dissipation	P _D	TA=25°C	1.15
		TA=70°C	0.75
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	T ≤ 10sec	52
		Steady State	100

SPP6507

ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-10\mu A$	-30			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4		-1.0		
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	uA	
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ C$			-10		
On-State Drain Current	$I_{D(on)}$	$V_{DS}=-5V, V_{GS}=-4.5V$	-4			A	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-2.8A$		0.085	0.105	Ω	
		$V_{GS}=-4.5V, I_D=-2.5A$		0.100	0.115		
		$V_{GS}=-2.5V, I_D=-1.5A$		0.135	0.150		
		$V_{GS}=-1.8V, I_D=-1.0A$		0.185	0.215		
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_D=-2.8A$		4.0		S	
Diode Forward Voltage	V_{SD}	$I_S=-1.2A, V_{GS}=0V$		-0.8	-1.2	V	
Dynamic							
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-4.5V$ $I_D=-2.0A$		5.8		nC	
Gate-Source Charge	Q_{gs}			0.8			
Gate-Drain Charge	Q_{gd}			1.5			
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		380		pF	
Output Capacitance	C_{oss}			55			
Reverse Transfer Capacitance	C_{rss}			40			
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=15\Omega$ $I_D=-1.0A, V_{GEN}=-10V$ $R_G=3\Omega$		6		ns	
	t_r			3.9			
Turn-Off Time	$t_{d(off)}$				40		
	t_f				15		